Supporting information:

Effect of Oxygen Flow Rate on Metal-to-Insulator Transition Characteristics in NbO_x-Based Selectors

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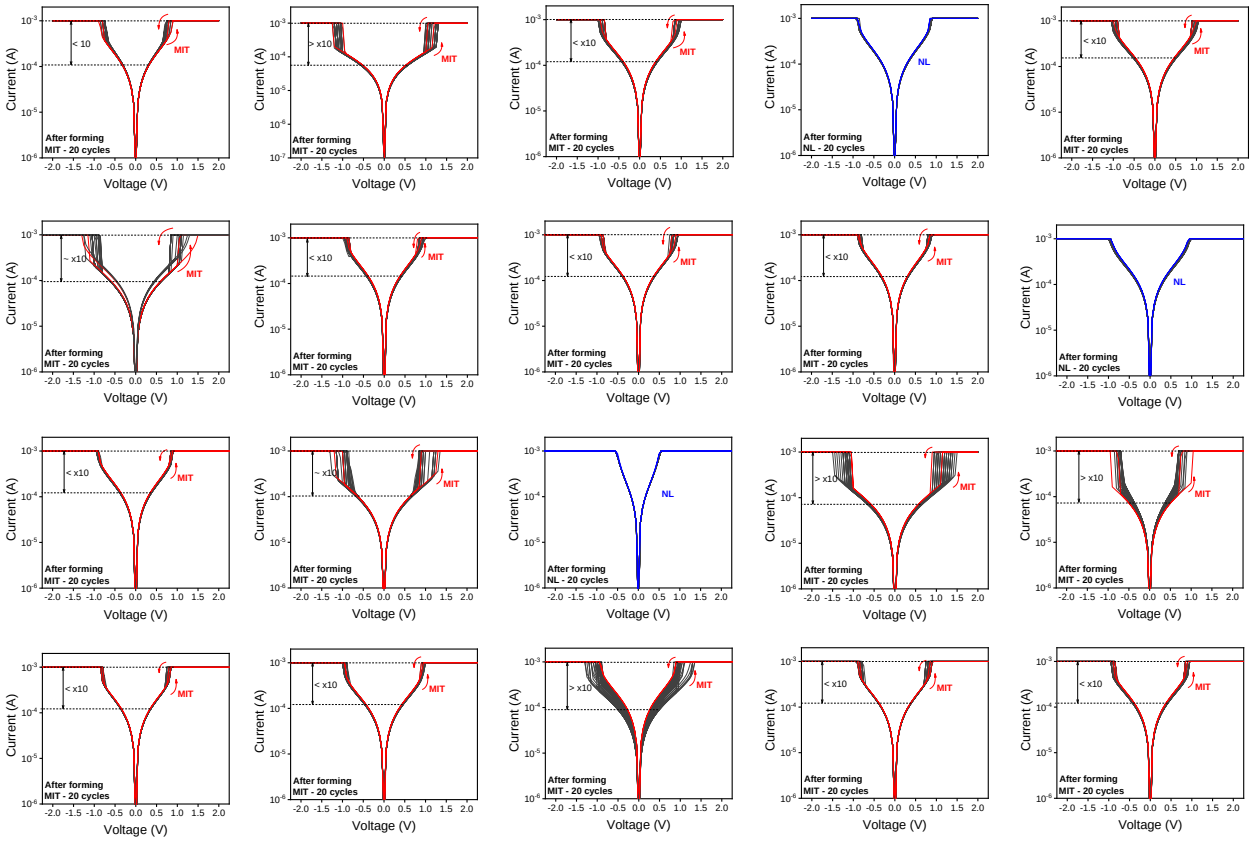

Figure S1. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

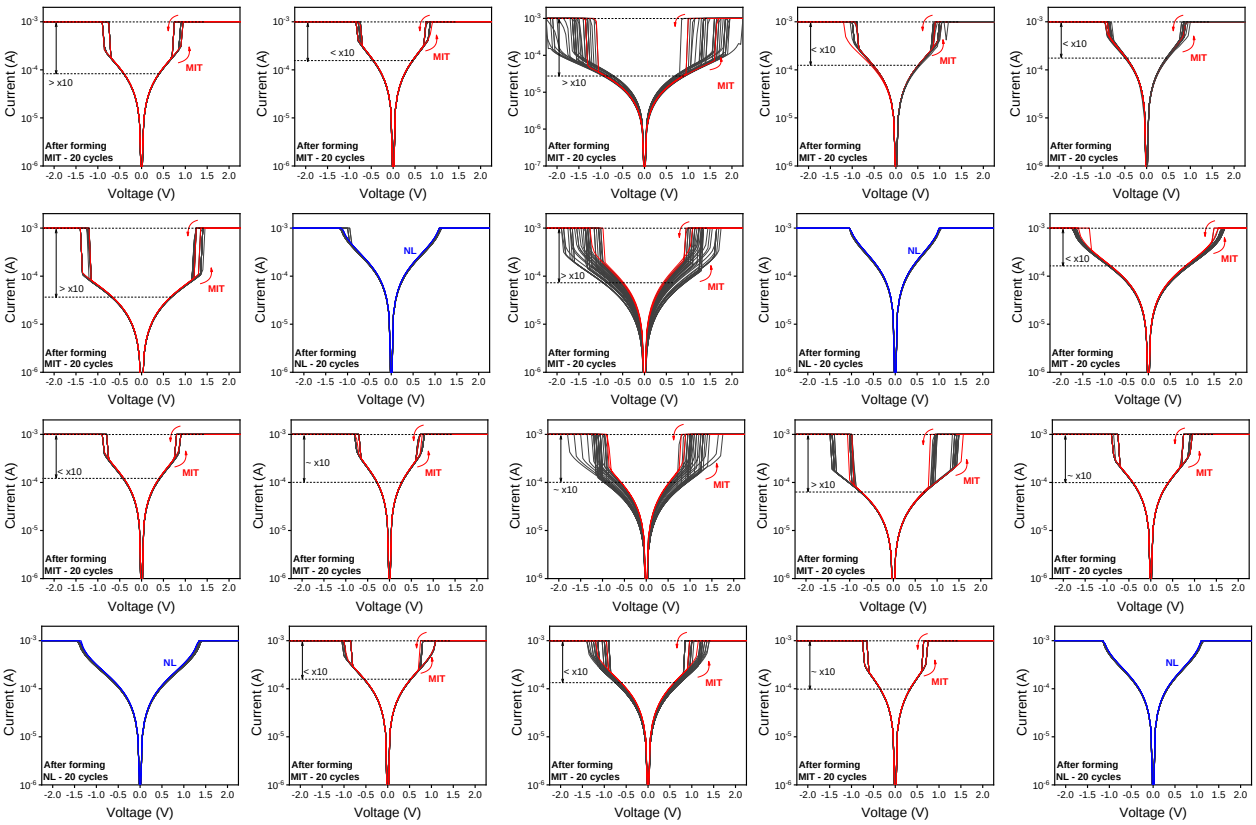

Figure S2. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 10 min.

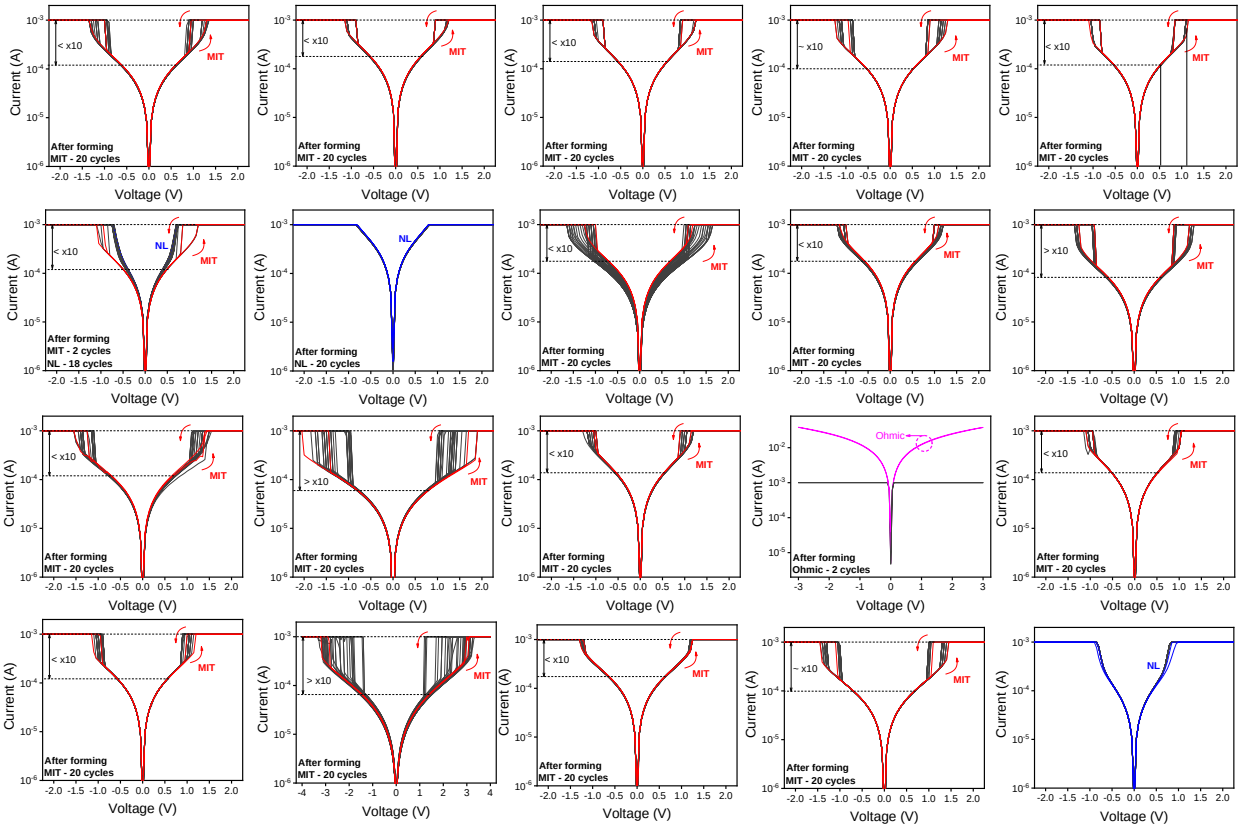

Figure S3. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 13 min.

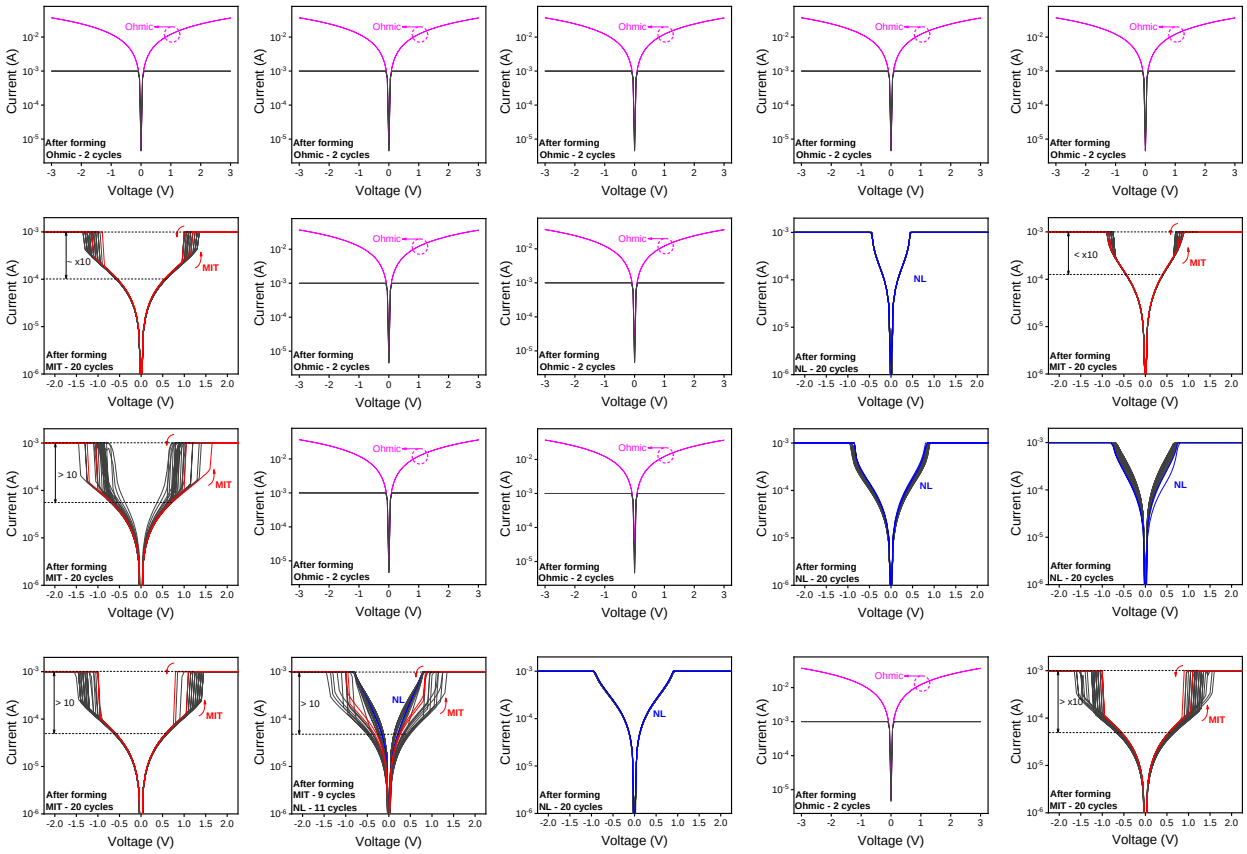

Figure S4. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 4.5 sccm of oxygen flow for 7 min.

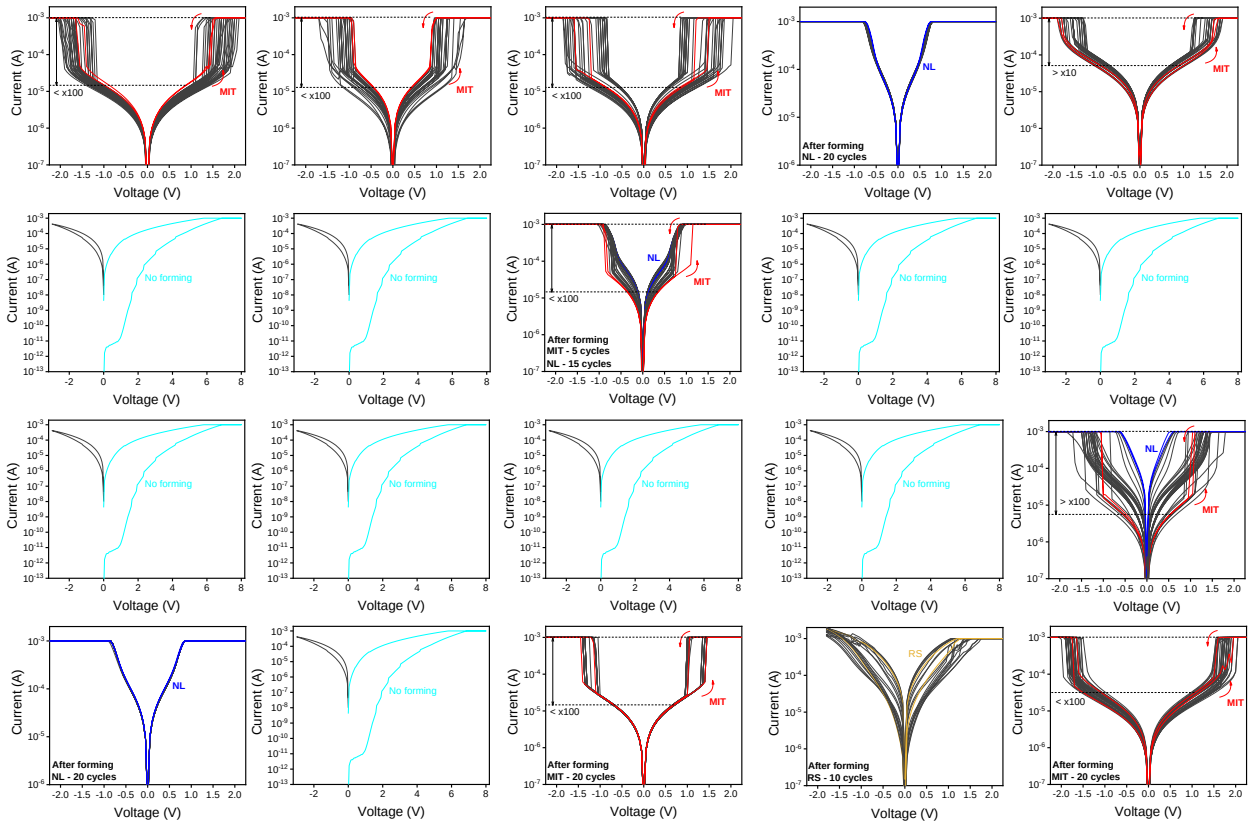

Figure S5. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 4.5 sccm of oxygen flow for 10 min.

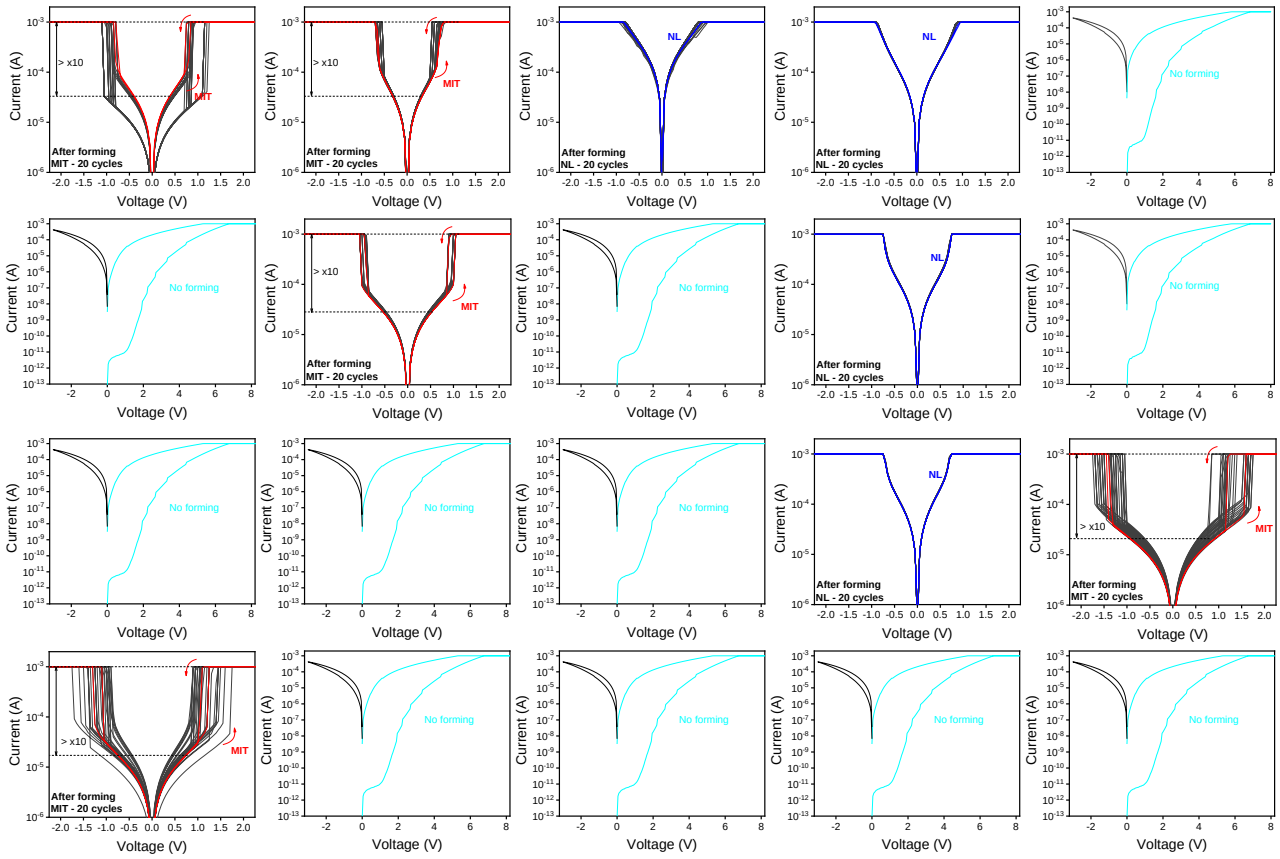

Figure S6. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 4.5 sccm of oxygen flow for 13 min.

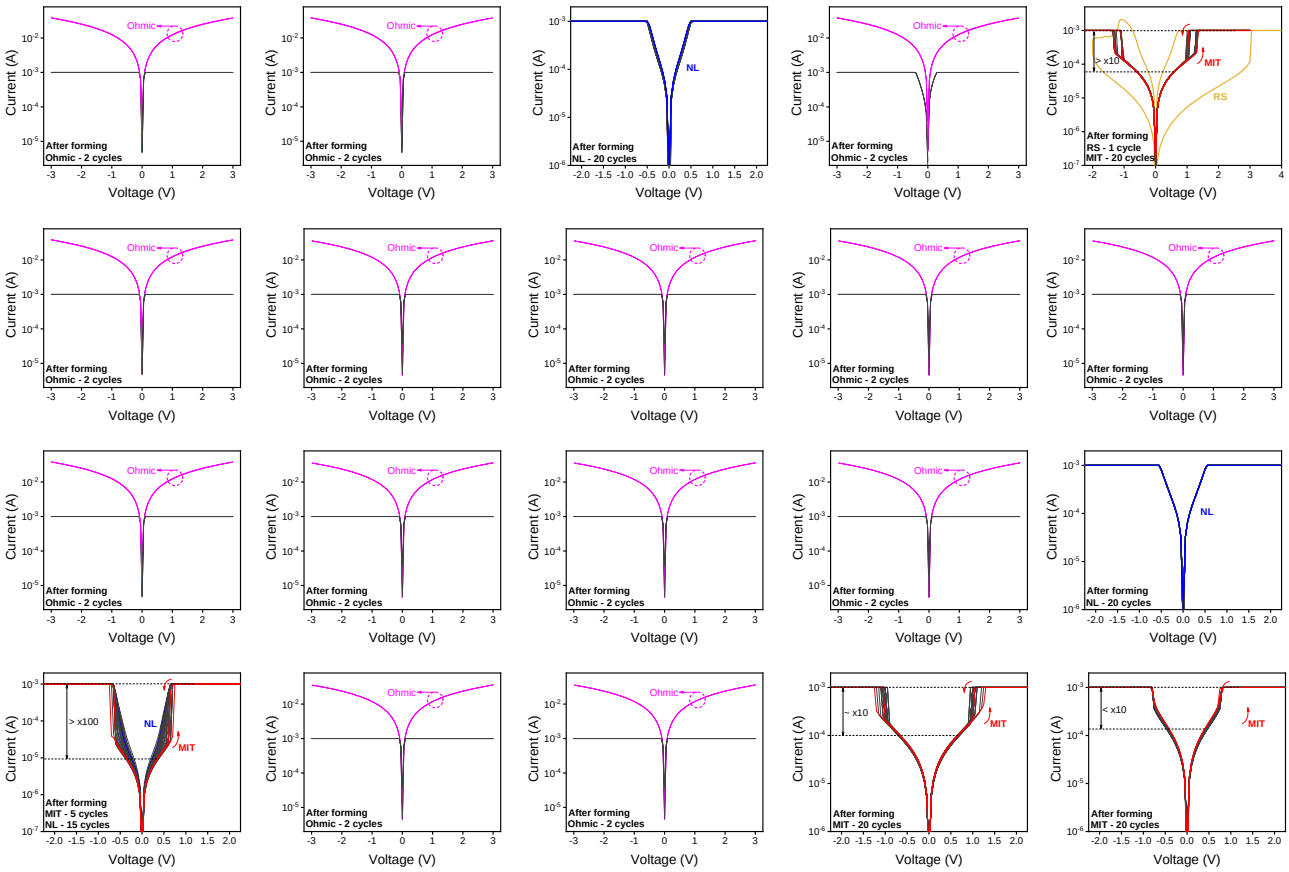

Figure S7. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 5.5 sccm of oxygen flow for 7 min.

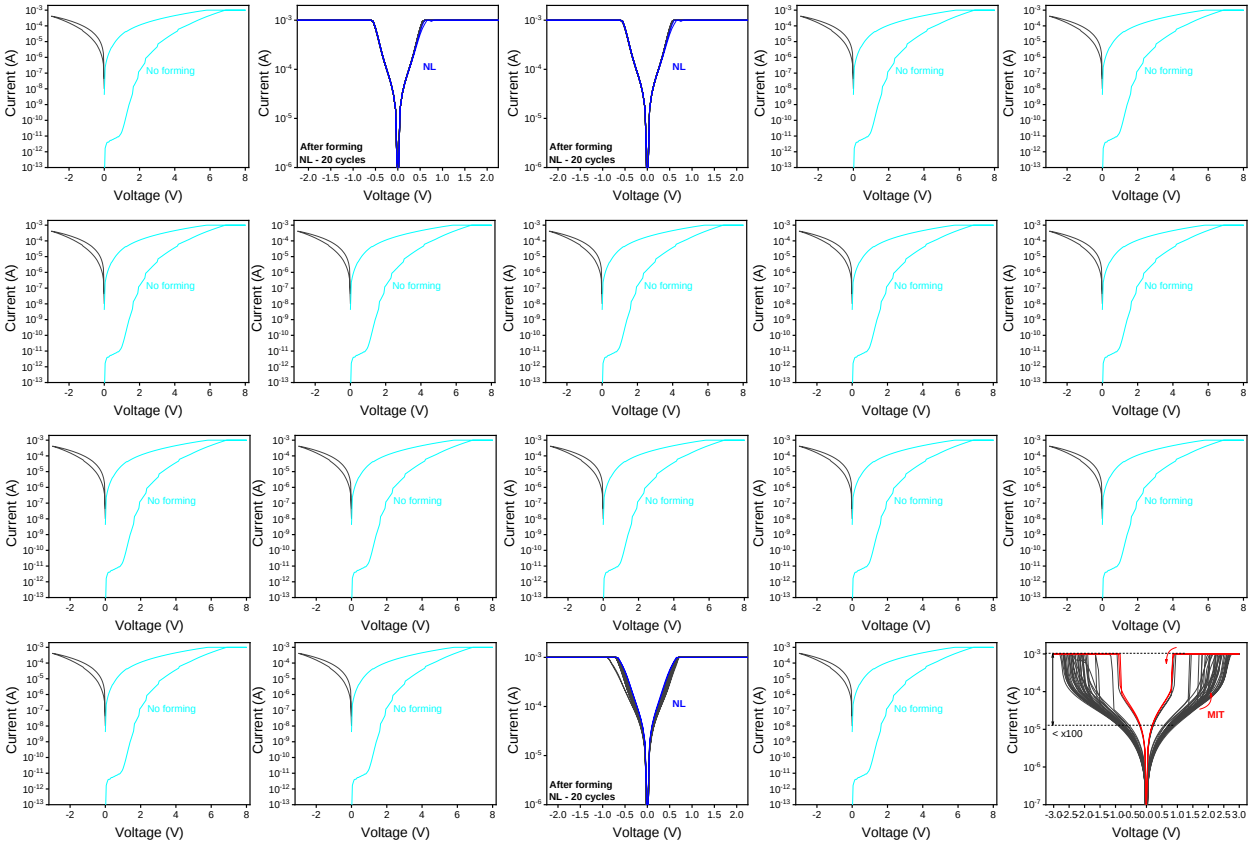

Figure S8. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 5.5 sccm of oxygen flow for 10 min.

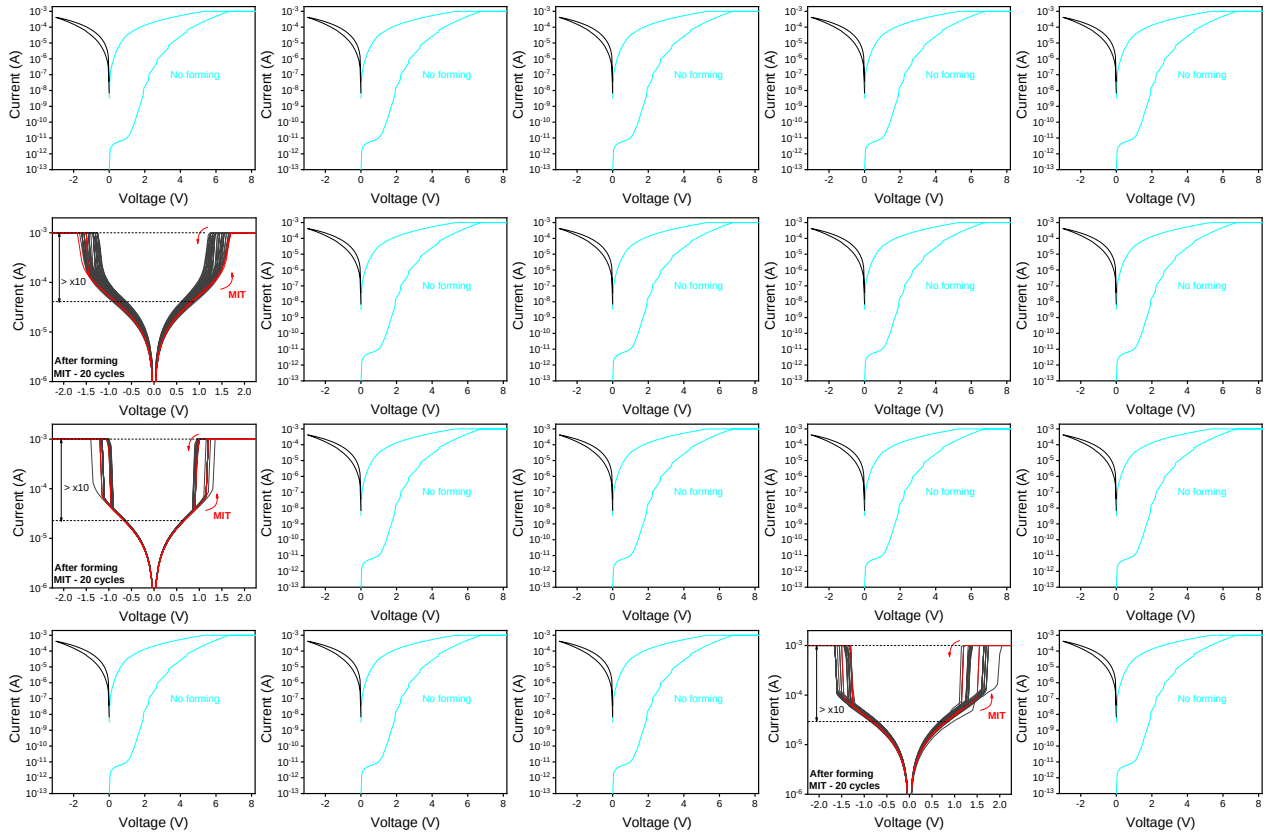

Figure S9. I-V curve measuring MIT characteristics in 20 cells of a device fabricated by depositing 5.5 sccm of oxygen flow for 13 min.

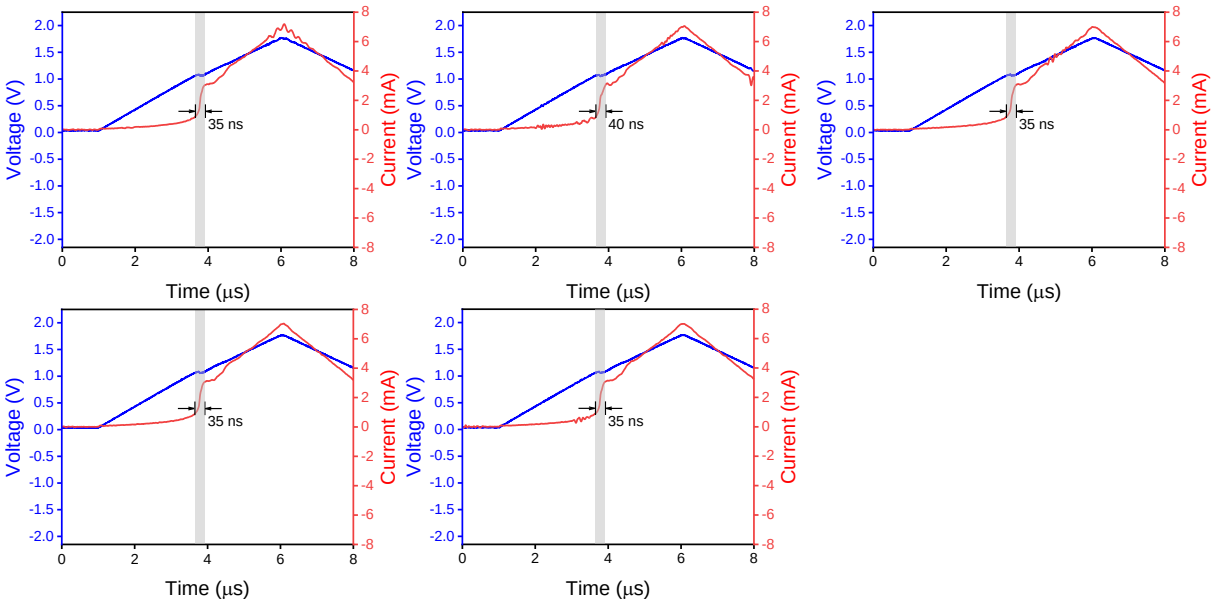

Figure S10. Switching time at 5 cells of a device deposited at oxygen flow rate of 3.5 sccm for 7 min.

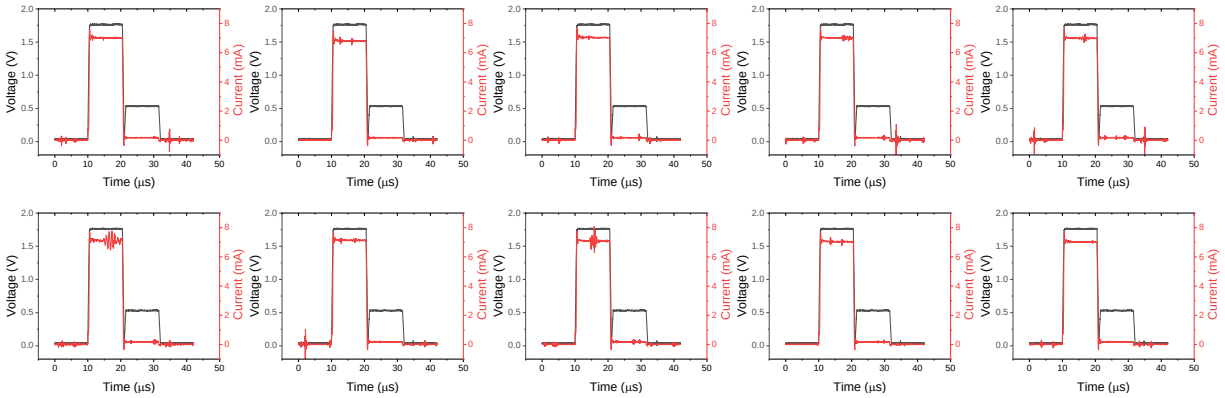

Figure S11. Recovery characteristics (50 ns) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

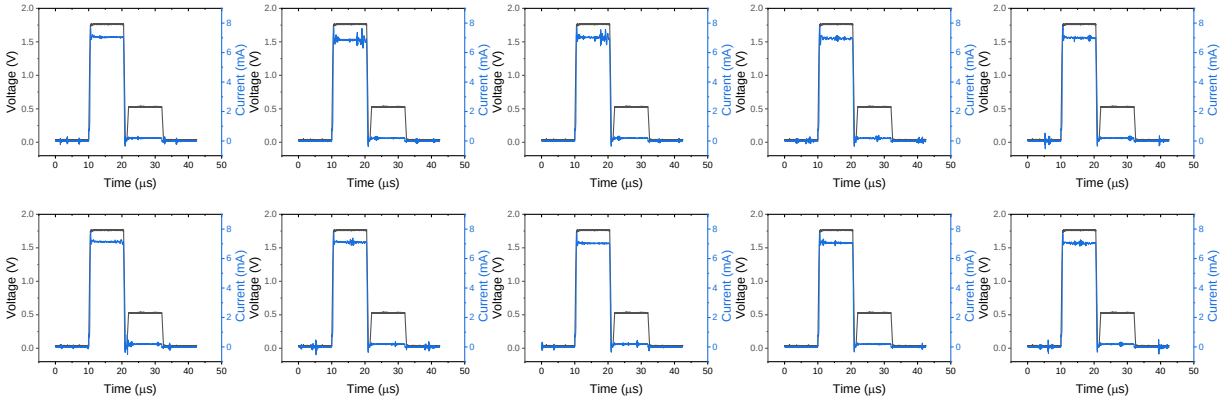

Figure S12. Recovery characteristics (500 ns) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

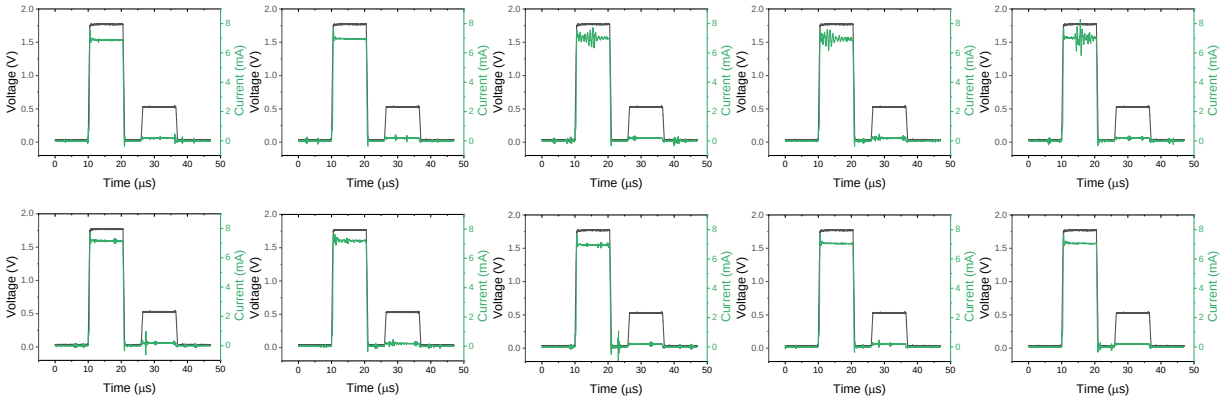

Figure S13. Recovery characteristics (5 μs) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

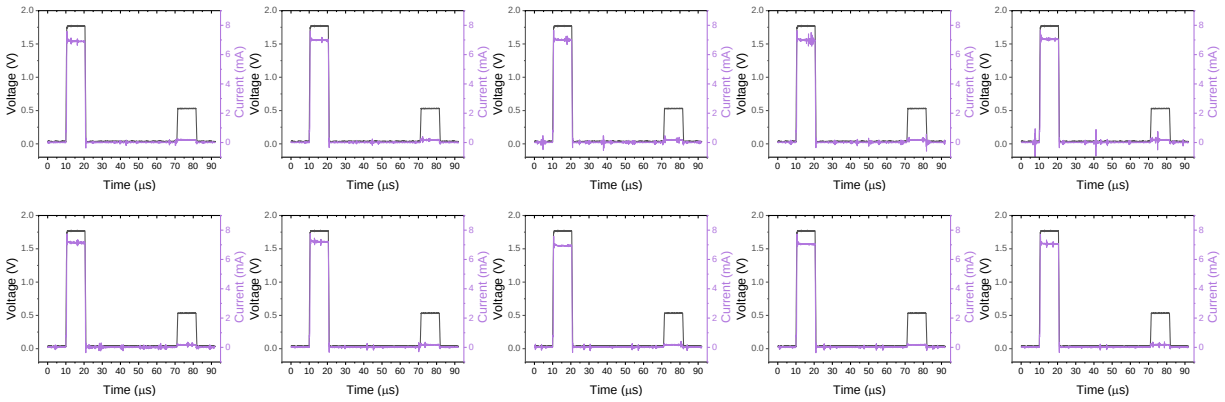

Figure S14. Recovery characteristics (50 μs) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

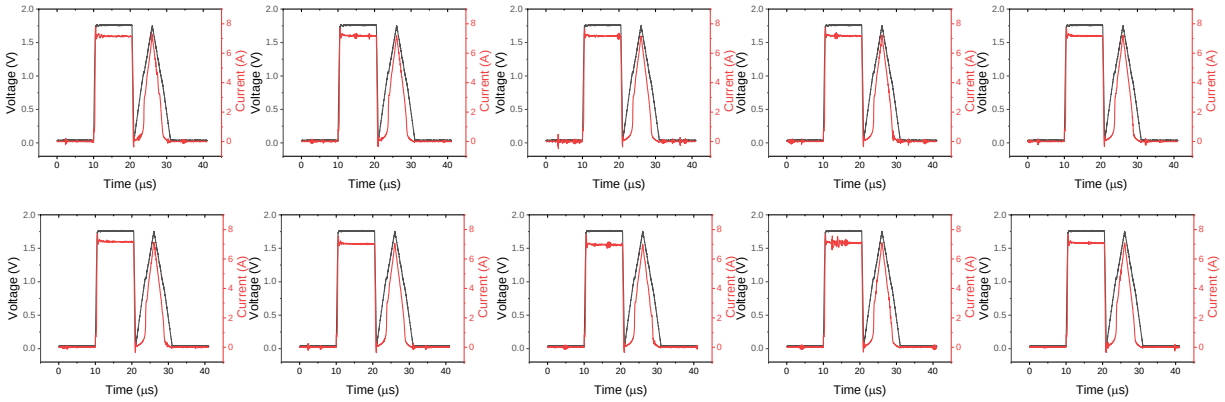

Figure S15. Drift characteristics (50 ns) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

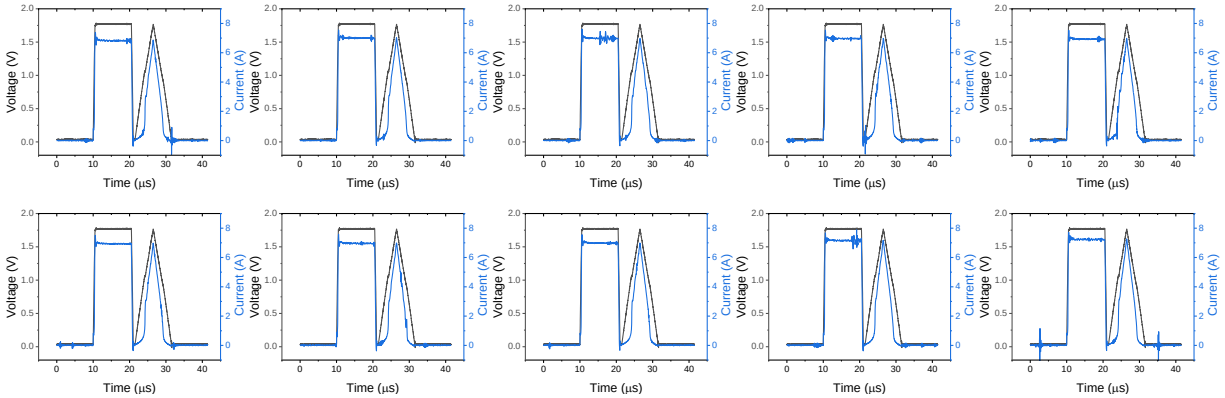

Figure S16. Drift characteristics (500 ns) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

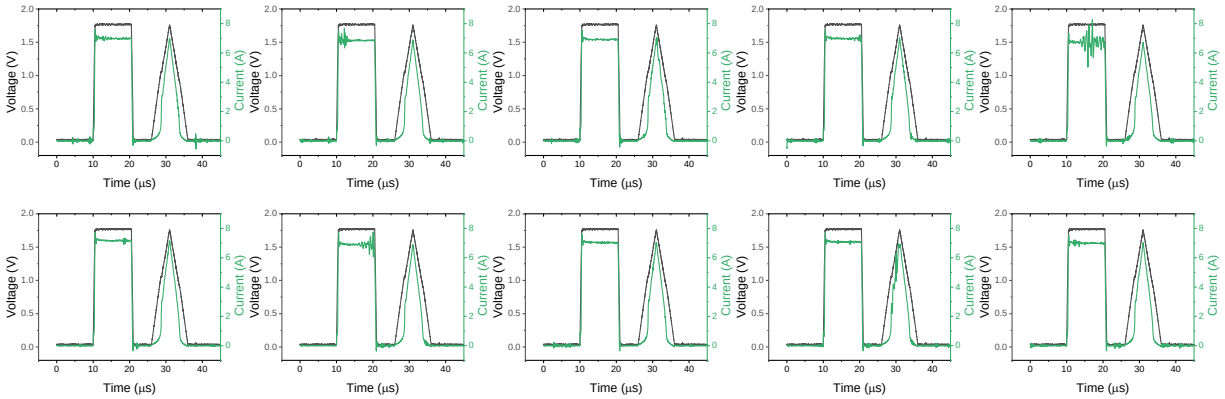

Figure S17. Drift characteristics (5 μs) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.

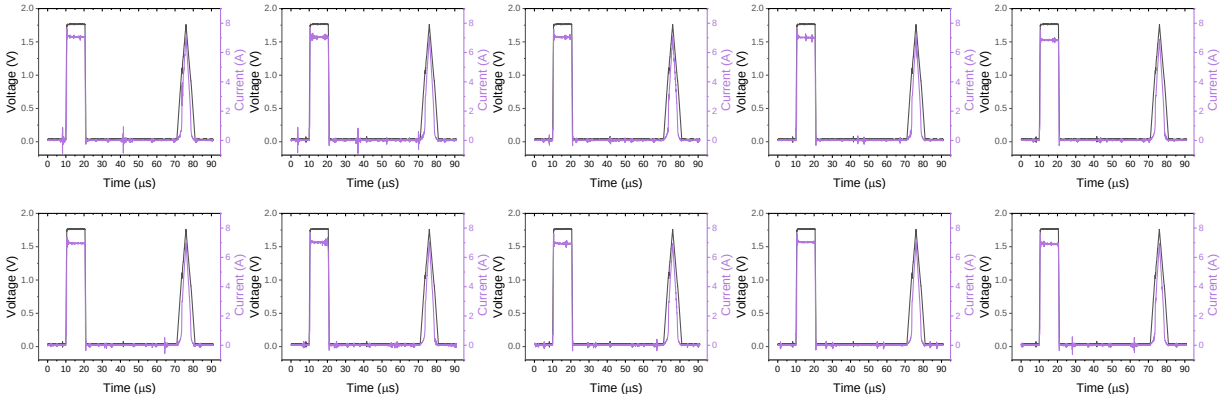

Figure S18. Drift characteristics (50 μs) in 20 cells of a device fabricated by depositing 3.5 sccm of oxygen flow for 7 min.